

The documentation and process conversion measures necessary to comply with this document shall be completed by 9 May 2010.

INCH-POUND

MIL-PRF-19500/291R
w/AMENDMENT 2
9 February 2010
SUPERSEDING
MIL-PRF-19500/291R
w/AMENDMENT 1
20 March 2008

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, SILICON, SWITCHING,
TYPES 2N2906A, 2N2906AL, 2N2907A, 2N2907AL, 2N2906AUA,
2N2907AUA, 2N2906AUB, 2N2906AUBC, 2N2907AUB, AND 2N2907AUBC, JAN,
JANTX, JANTXV, JANJ, JANS, JANSM, JANSD, JANSP, JANSL, JANSR, JANSF,
JANSJ, JANSH JANHCB, JANHCD JANKCB, JANKCD JANKCBM, JANKCBD,
JANKCBP, JANKCBL, JANKCBR, JANKCBF, JANKCBG, AND JANKCBH

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

The requirements for acquiring the product described herein shall consist of
this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for PNP, silicon, switching transistors. Five levels of product assurance are provided for each encapsulated device type as specified in MIL-PRF-19500 and two levels of product assurance are provided for each unencapsulated device type. RHA level designators "M", "D", "P", "L", "R", "F", "G", and "H" are appended to the device prefix to identify devices which have passed RHA requirements.

1.2 Physical dimensions. See figure 1 (similar to a TO-18), figures 2, 3, and 4 (surface mount case outlines UA, UB, and UBC), and figures 5 and 6 (JANHCB and JANKCB).

1.3 Maximum ratings. Unless otherwise specified $T_A = +25^{\circ}\text{C}$.

Types	I_C	V_{CBO}	V_{EBO}	V_{CEO}	T_J and T_{STG}
	<u>mA dc</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>$^{\circ}\text{C}$</u>
All devices	600	60	5	60	-65 to +200

SEMICONDUCTOR DEVICE, TRANSISTOR, PNP, SILICON, SWITCHING,
TYPES 2N2906A, 2N2906AL, 2N2907A, 2N2907AL, 2N2906AUA,

* Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dscclia.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <https://assist.daps.dla.mil>.

MIL-PRF-19500/291R
w/AMENDMENT 2

1.3 Maximum ratings. Unless otherwise specified $T_A = +25^\circ\text{C}$. - Continued.

Types	P_T $T_A = +25^\circ\text{C}$ (1) (2)	P_T $T_C = +25^\circ\text{C}$ (1) (2)	P_T $T_{SP(IS)} =$ $+25^\circ\text{C}$ (1) (2)	P_T $T_{SP(AM)} =$ $+25^\circ\text{C}$ (1) (2)	$R_{\theta JA}$ (2) (3)	$R_{\theta JC}$ (2) (3)	$R_{\theta JSP(IS)}$ (2) (3)	$R_{\theta JSP(AM)}$ (2) (3)
	<u>W</u>	<u>W</u>	<u>W</u>	<u>W</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>	<u>$^\circ\text{C/W}$</u>
2N2906A, L,	0.5	1.0	N/A	N/A	325	150	N/A	N/A
2N2907A, L	0.5	1.0	N/A	N/A	325	150	N/A	N/A
2N2906AUA,	0.5 (4)	N/A	1.0	1.5	325 (4)	N/A	110	40
2N2907AUA	0.5 (4)	N/A	1.0	1.5	325 (4)	N/A	110	40
2N2906AUB,	0.5 (4)	N/A	1.0	N/A	325 (4)	N/A	90	N/A
2N2907AUB	0.5 (4)	N/A	1.0	N/A	325 (4)	N/A	90	N/A
2N2906AUBC	0.5 (4)	N/A	1.0	N/A	325 (4)	N/A	90	N/A
, 2N2907AUBC	0.5 (4)	N/A	1.0	N/A	325 (4)	N/A	90	N/A

(1) For derating, see figures 7, 8, 9, 10, and 11.

(2) See 3.3 for abbreviations.

(3) For thermal curves, see figures 12, 13, 14, 15, and 16.

(4) For non-thermal conductive PCB or unknown PCB surface mount conditions in free air, substitute figures 7 and 12 for the UA, UB, and UBC package and use $R_{\theta JA}$.

1.4 Primary electrical characteristics. Unless otherwise specified $T_A = +25^\circ\text{C}$.

h_{FE} at $V_{CE} = 10\text{ V dc}$										
	h_{FE1} $I_C = 0.1\text{ mA dc}$		h_{FE2} $I_C = 1.0\text{ mA dc}$		h_{FE3} $I_C = 10\text{ mA dc}$		h_{FE4} (1) $I_C = 150\text{ mA dc}$		h_{FE5} (1) $I_C = 500\text{ mA dc}$	
	2N2906A, L, UA,UB, UBC	2N2907A, L, UA,UB, UBC	2N2906A, L, UA,UB, UBC	2N2907A, L, UA,UB, UBC	2N2906A, L, UA,UB, UBC	2N2907A, L, UA,UB, UBC	2N2906A, L, UA,UB, UBC	2N2907A, L, UA,UB, UBC	2N2906A, L, UA,UB, UBC	2N2907A, L, UA,UB, UBC
Min	40	75	40	100	40	100	40	100	40	50
Max			175	450			120	300		

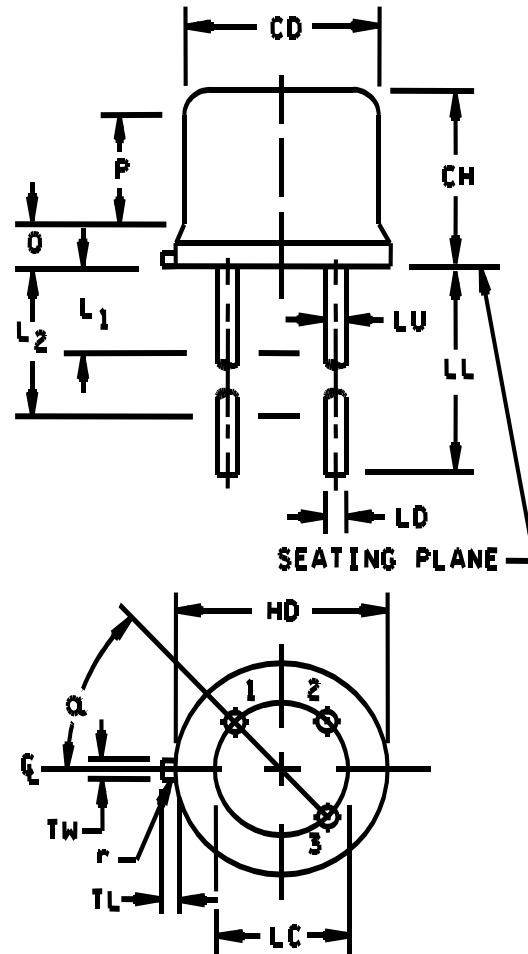
Types	Limit	$ h_{fe} $ $f = 100\text{ MHz}$ $V_{CE} = 20\text{ V dc}$, $I_C = 20\text{ mA dc}$	C_{obo} $100\text{ kHz} \leq f \leq 1\text{ MHz}$ $V_{CB} = 10\text{ V dc}$, $I_E = 0$	Switching (saturated)	
				t_{on} See figure 17	t_{off} See figure 18
2N2906A, 2N2907A, L, UA, UB, UBC	Min Max	2.0	<u>pF</u> 8	<u>ns</u> 45	<u>ns</u> 300

Types	Limits	$V_{CE(sat)1}$ (1) $I_C = 150\text{ mA dc}$ $I_B = 15\text{ mA dc}$	$V_{CE(sat)2}$ (1) $I_C = 500\text{ mA dc}$ $I_B = 50\text{ mA dc}$	$V_{BE(sat)1}$ (1) $I_C = 150\text{ mA dc}$ $I_B = 15\text{ mA dc}$	$V_{BE(sat)2}$ (1) $I_C = 500\text{ mA dc}$ $I_B = 50\text{ mA dc}$
2N2906A, 2N2907A, L, UA, UB, UBC	Min Max	<u>V dc</u> 0.4	<u>V dc</u> 1.6	<u>V dc</u> 0.6 1.3	<u>V dc</u> 2.6

(1) Pulsed see 4.5.1.

MIL-PRF-19500/291R
w/AMENDMENT 2

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.170	.210	4.32	5.33	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7,8
LL	.500	.750	12.70	19.05	7,8,13
LU	.016	.019	0.41	0.48	7,8
L ₁		.050		1.27	7,8
L ₂	.250		6.35		7,8
P	.100		2.54		
Q		.030		0.76	5
TL	.028	.048	0.71	1.22	3,4
TW	.036	.046	0.91	1.17	3
r		.010		0.25	10
α	45° TP		45° TP		6

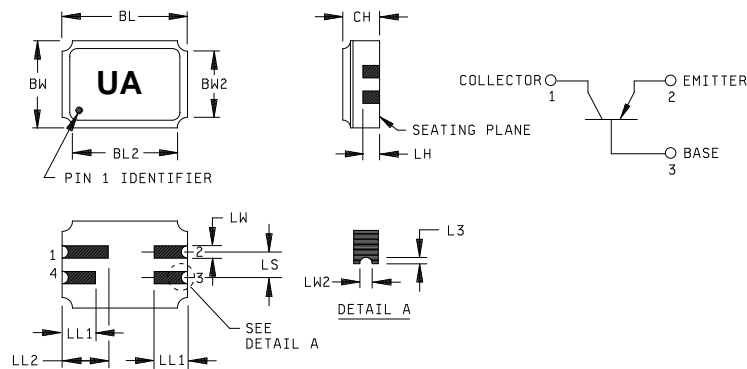


NOTES:

1. Dimension are in inches.
2. Millimeters are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 inch (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
7. Dimension LU applies between L₁ and L₂. Dimension LD applies between L₂ and LL minimum. Diameter is uncontrolled in L₁ and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.
12. Lead 1 = emitter, lead 2 = base, lead 3 = collector.
13. For L suffix devices, dimension LL = 1.5 inches (38.10 mm) min. and 1.75 inches (44.45 mm) max.

FIGURE 1. Physical dimensions (similar to TO-18).

MIL-PRF-19500/291R
w/AMENDMENT 2



Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BL	.215	.225	5.46	5.71	
BL2		.225		5.71	
BW	.145	.155	3.68	3.93	
BW2		.155		3.93	
CH	.061	.075	1.55	1.90	3
L3	.003	.007	0.08	0.18	5
LH	.029	.042	0.74	1.07	
LL1	.032	.048	0.81	1.22	
LL2	.072	.088	1.83	2.23	
LS	.045	.055	1.14	1.39	
LW	.022	.028	0.56	0.71	
LW2	.006	.022	0.15	0.56	5

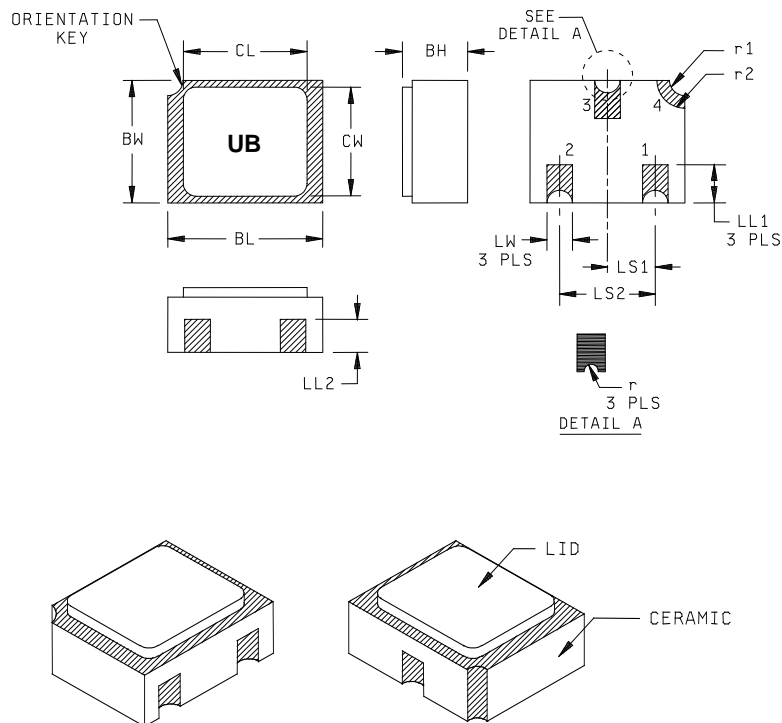
Pin no.	1	2	3	4
Transistor	Collector	Emitter	Base	N/C

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Dimension "CH" controls the overall package thickness. When a window lid is used, dimension "CH" must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
4. The corner shape (square, notch, radius) may vary at the manufacturer's option, from that shown on the drawing.
5. Dimensions "LW2" minimum and "L3" minimum and the appropriate castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on bottom two layers, optional on top ceramic layer.) Dimension "LW2" maximum and "L3" maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.
6. The coplanarity deviation of all terminal contact points, as defined by the device seating plane, shall not exceed .006 inch (0.15mm) for solder dipped leadless chip carriers.
7. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 2. Physical dimensions, surface mount (UA version).

MIL-PRF-19500/291R
w/AMENDMENT 2



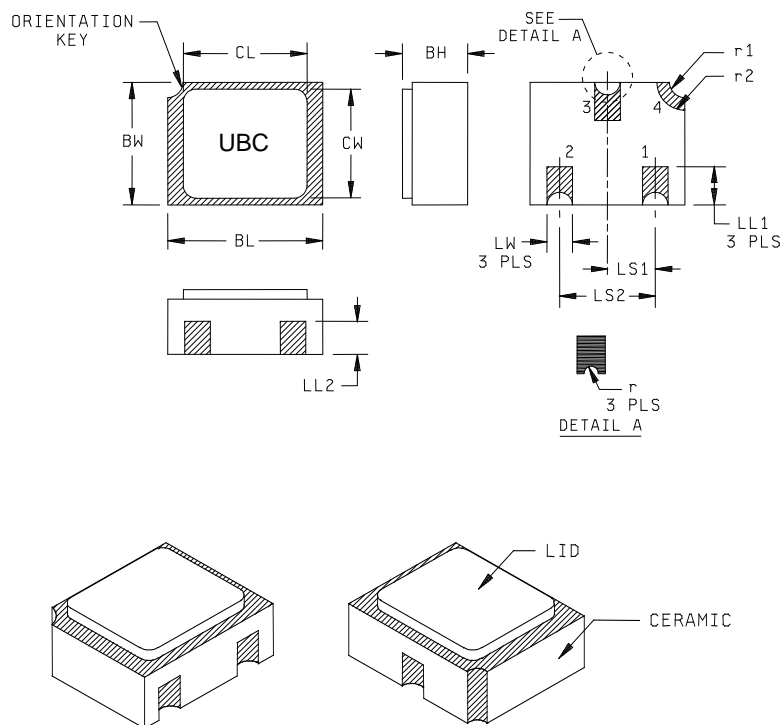
Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	
LS1	.036	.040	0.91	1.02	
LS2	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r1		.012		.305	
r2		.022		.559	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
4. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

* FIGURE 3. Physical dimensions, surface mount (UB version).

MIL-PRF-19500/291R
w/AMENDMENT 2

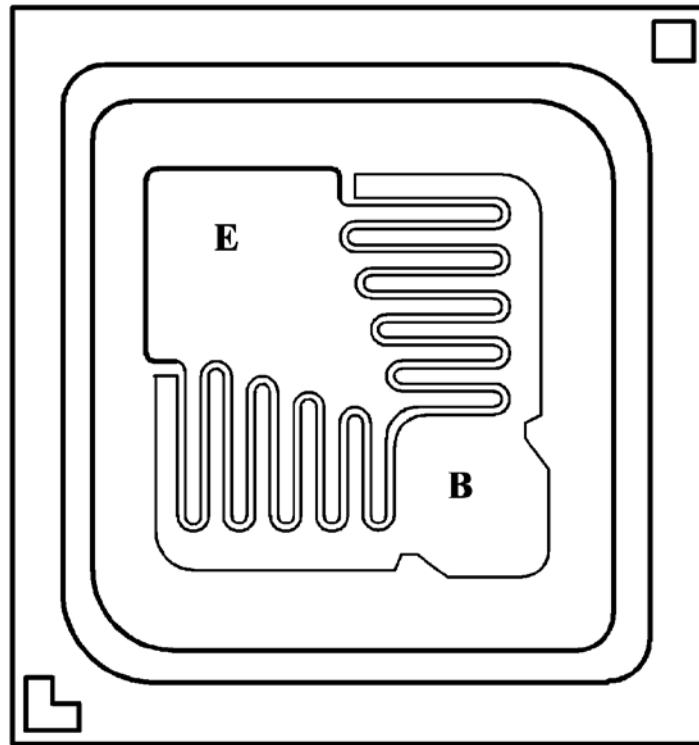


Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.046	.071	1.17	1.80	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.96	
LL2	.017	.035	0.43	0.89	
LS1	.036	.040	0.91	1.02	
LS2	.071	.079	1.81	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r1		.012		.305	
r2		.022		.559	

NOTES:

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Hatched areas on package denote metallized areas.
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

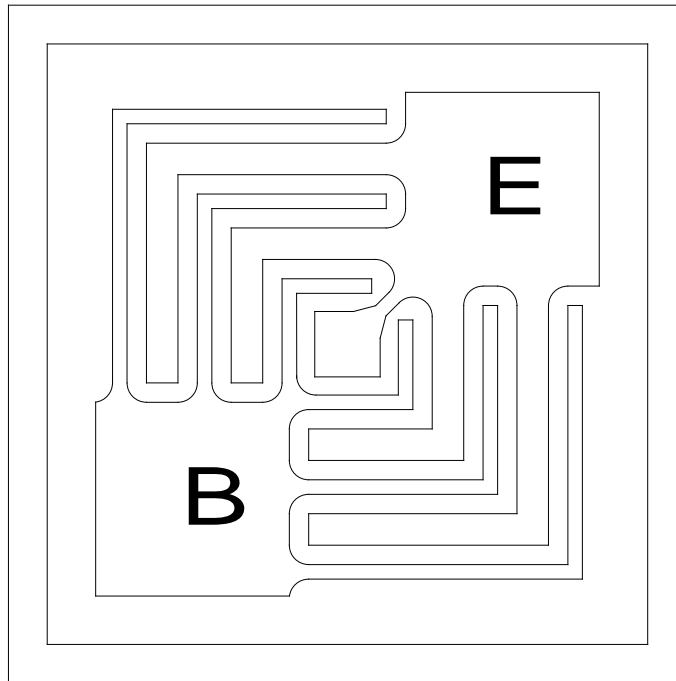
* FIGURE 4. Physical dimensions, surface mount (UBC version, ceramic lid).



1. Chip size: .023 x .023 inch \pm .002 inch (0.584 mm x 0.584 mm \pm 0.0508 mm).
2. Chip thickness: .010 \pm .0015 inch (0.254 mm \pm 0.038 mm).
3. Top metal: Aluminum 15,000 Å minimum, 18,000 Å nominal.
4. Back metal:
 - A. Al/Ti/Ni/Ag 15kÅ/5kÅ/10kÅ/10kÅ.
 - B. Gold 2.5 kÅ minimum, 3.0 kÅ nominal.
 - C. Eutectic Die Mount - No metal.
5. Glassivation: Si₃N₄ 2kÅ minimum, 2.2k nominal.
6. Backside: Collector.
7. Bonding pad:
 - B = .0042 x .0042 inch (0.107 mm x 0.107 mm).
 - E = .0042 x .0042 inch (0.107 mm x 0.107 mm).

FIGURE 5. JANHC and JANKC (B-version) die dimensions.

MIL-PRF-19500/291R
w/AMENDMENT 2



- | | |
|-------------------|--|
| 1. Die size: | .020 x .020 inch square (0.508 mm x 0.508 mm). |
| 2. Die thickness: | .008 \pm .0016 inch (0.203 mm \pm 0.041 mm). |
| 3. Base pad: | .004 x .004 inch (0.101 mm x 0.101 mm). |
| 4. Emitter pad: | .004 x .004 inch (0.101 mm x 0.101 mm). |
| 5. Back metal | Gold, 6,500 \pm 1,950 Å. |
| 6. Top metal: | Aluminum, 20,000 \pm 2,000 Å. |
| 7. Back side: | Collector. |
| 8. Glassivation: | SiO ₂ , 7,500 \pm 1,500 Å. |

FIGURE 6. JANHC and JANKC (D-version) die dimensions.

MIL-PRF-19500/291R
w/AMENDMENT 2

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3, 4, and 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, and 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

* (Copies of these documents are available online at <https://assist.daps.dla.mil/quicksearch> or <https://assist.daps.dla.mil> or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

* 2.3 Order of precedence. Unless otherwise noted herein or in the contract, in the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500 and as follows.

PCB	Printed circuit board
$R_{\theta JA}$	Thermal resistance junction to ambient.
$R_{\theta JC}$	Thermal resistance junction to case.
$R_{\theta JSP(AM)}$	Thermal resistance junction to solder pads (adhesive mount to PCB).
$R_{\theta JSP(IS)}$	Thermal resistance junction to solder pads (infinite sink mount to PCB).
$T_{SP(AM)}$	Temperature of solder pads (adhesive mount to PCB).
$T_{SP(IS)}$	Temperature of solder pads (infinite sink mount to PCB).
UA, UB, UBC	Surface mount case outlines (see figures 2, 3, and 4).

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500, and on figures 1, 2, 3, 4, 5, and 6 herein. Epoxy die attach may be used when a moisture monitor plan has been submitted and approved by the qualifying activity.

3.4.1 Lead finish. Lead finish shall be solderable as defined in MIL-PRF-19500. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

MIL-PRF-19500/291R
w/AMENDMENT 2

3.5 Radiation hardness assurance (RHA). Radiation hardness assurance requirements, PIN designators, and test levels shall be as defined in MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table I herein.

3.8 Marking. Marking shall be in accordance with MIL-PRF-19500, except for the UB suffix package. Marking on the UB package shall consist of an abbreviated part number, the date code, and the manufacturer's symbol or logo. The prefixes JAN, JANTX, JANTXV, JANJ, and JANS can be abbreviated as J, JX, JV, JJ, and JS respectively. The "2N" prefix and the "AUB" and "AUBC" suffix can also be omitted. The radiation hardened designator M, D, P, L, R, F, G, or H shall immediately precede (or replace) the device "2N" identifier (depending upon degree of abbreviation required).

3.9 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.4 and tables I, II, and III).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500, and as specified herein.

4.2.1 JANJ devices. For JANJ level, 3.3.1 through 3.3.1.3 of MIL-PRF-19500 shall apply, except as modified herein. Supplier imposed requirements, as well as alternate screens, procedures, or controls shall be documented in the QM plan and must be submitted to the qualifying activity for approval. When alternate screens, procedures, or controls are used in lieu of the JANJ screens herein, equivalency shall be proven and documented in the QM plan. Radiation characterization may be submitted in the QM plan at the option of the manufacturer; however, 3.3.1.1 of MIL-PRF-19500 is not required. Die lot controls and rework requirements shall be in accordance with 3.13 of MIL-PRF-19500 and D.3.13.2.1 for JANS level. Lot formation and conformance inspection requirements for JANJ shall be those used for JANTXV devices as a minimum.

4.2.2 JANJ qualification. For JANJ qualification, 4.4.2.2 herein shall be performed as required by the qualifying activity. A JANS certified supplier may supply JANJ product utilizing the JANJ screening flow in 4.3 herein.

4.2.3 JANHC and JANKC qualification. JANHC and JANKC qualification inspection shall be in accordance with MIL-PRF-19500.

4.2.4 Group E qualification. Group E inspection shall be performed for qualification or re-qualification only. In case qualification was awarded to a prior revision of the specification sheet that did not request the performance of table III tests, the tests specified in table III herein that were not performed in the prior revision shall be performed on the first inspection lot of this revision to maintain qualification.

MIL-PRF-19500/291R
w/AMENDMENT 2

4.3 Screening (JANTX, JANTXV, JANJ, and JANS levels only). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANJ level
1b	Required	Required
2	Optional	Optional
3a 3b 3c	Required Not applicable Required method 3131 of MIL-STD-750 (1)	Required Not applicable Required method 3131 of MIL-STD-750 (1)
4	Required	Optional
5	Required	Required (one pass minimum)
6	Not applicable	Not applicable
8	Required	Not required
9	I_{CBO2} , h_{FE4} , read and record	I_{CBO2} , h_{FE4} (bin and cell)
10	24 hours minimum	24 hours minimum
11	I_{CBO2} ; h_{FE4} ; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater. Δh_{FE4} = ± 15 percent	I_{CBO2} ; h_{FE4} ; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater. Δh_{FE4} = ± 15 percent
12	See 4.3.2	See 4.3.2
(2) 13	Subgroups 2 and 3 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent	Subgroups 2 and 3 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent
15	Required	Required - attributes data only, film or non-film techniques may be utilized
16	Required	Required

See notes at end of screen table.

MIL-PRF-19500/291R
w/AMENDMENT 2

4.3 Screening (JANTX, JANTXV, JANJ, and JANS levels only) - Continued.

Screen (see table IV of MIL-PRF-19500)	Measurement
	JANTXV and JANTX level
1b	Required (JANTXV only)
2	Optional
3a	Required
3b (1) 3c	Not applicable Required method 3131 of MIL-STD-750.
4	Optional
5	Not required
6	Not applicable
8	Not required
9	Not applicable
10	24 hours minimum
11	I_{CBO2} , h_{FE4}
12	See 4.3.2
(2) 13	Subgroup 2 of table I herein; ΔI_{CBO2} = 100 percent of initial value or 5 nA dc, whichever is greater; Δh_{FE4} = ± 15 percent
15 and 16	Not required

- (1) Shall be performed anytime after temperature cycling, screen 3a; and does not need to be repeated in screening requirements.
- (2) PDA = 5 percent for screen 13, applies to ΔI_{CBO2} , Δh_{FE4} , I_{CBO2} , and h_{FE4} . Thermal impedance ($Z_{\theta JX}$) is not required in screen 13.

4.3.1 Screening (JANH and JANKC). Screening of JANHC and JANKC die shall be in accordance with MIL-PRF-19500, "Discrete Semiconductor Die/Chip Lot Acceptance". Burn-in duration for the JANKC level follows JANS requirements; the JANHC follows JANTX requirements.

MIL-PRF-19500/291R
w/AMENDMENT 2

4.3.2 Power burn-in conditions. Power burn-in conditions are as follows: $V_{CB} = 10 - 30$ V dc. Power shall be applied to achieve $T_J = +135^\circ\text{C}$ minimum using a minimum $P_D = 75$ percent of P_T maximum, T_A ambient rated as defined in 1.3. With approval of the qualifying activity and preparing activity, alternate burn-in criteria (hours, bias conditions, T_J , and mounting conditions) for JANTX and JANTXV quality levels may be used. A justification demonstrating equivalence is required. In addition, the manufacturing site's burn-in data and performance history will be essential criteria for burn-in modification approval.

4.3.3 Thermal impedance measurements. The thermal impedance measurements shall be performed in accordance with method 3131 of MIL-STD-750 using the guidelines in that method for determining I_M , I_H , t_H , and t_{MD} (and V_C where appropriate). The thermal impedance limit used in screen 3c of 4.3 herein and subgroup 2 of table I shall comply with the thermal impedance graphs in figures 12, 13, 14, 15, and 16 (less than or equal to the curve value at the same t_H time) and shall be less than the process determined statistical maximum limit as outlined in method 3131. See table III, subgroup 4 herein.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500, and as specified herein. If alternate screening is being performed in accordance with MIL-PRF-19500, a sample of screened devices shall be submitted to and pass the requirements of subgroups 1 and 2, of table I herein, inspection only (table E-VIb, group B, subgroup 1 is not required to be performed again if group B has already been satisfied in accordance with 4.4.2).

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500, and table I herein. Group A inspection for JANJ shall be in accordance with JANTXV of MIL-PRF-19500 and table I herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VIa (JANS) of MIL-PRF-19500 and 4.4.2.1 herein. Electrical measurements (end-points) and delta requirements shall be in accordance with table I, subgroup 2 and 4.5.3 herein. See 4.4.2.2 herein for JAN, JANTX, JANTXV, and JANJ group B testing. Electrical measurements (end-points) and delta requirements for JAN, JANTX, JANTXV, and JANJ shall be after each step in 4.4.2.2 and shall be in accordance with table I, subgroup 2 and 4.5.3 herein.

4.4.2.1 Group B inspection, table E-VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B4	1037	$V_{CB} = 10 - 30$ V dc. Adjust device current, or power, to achieve a minimum ΔT_J of 100°C .
B5	1027	$V_{CB} = 10$ V dc; $P_D \geq 100$ percent of maximum rated P_T (see 1.3). (NOTE: If a failure occurs, resubmission shall be at the test conditions of the original sample.) Option 1: 96 hours minimum sample size in accordance with MIL-PRF-19500, table E-VIa, adjust T_A or P_D to achieve $T_J = +275^\circ\text{C}$ minimum. Option 2: 216 hours minimum, sample size = 45, $c = 0$; adjusted T_A or P_D to achieve a $T_J = +225^\circ\text{C}$ minimum.
B6	3131	$R_{\theta JA}$, $R_{\theta JC}$ only (see 1.3).

MIL-PRF-19500/291R
w/AMENDMENT 2

4.4.2.2 Group B inspection, (JAN, JANTX, JANTXV, and JANJ). Separate samples may be used for each step. In the event of a lot failure, the resubmission requirements of MIL-PRF-19500 shall apply. In addition, all catastrophic failures during conformance inspection shall be analyzed to the extent possible to identify root cause and corrective action. Whenever a failure is identified as wafer lot and wafer processing related, the entire wafer lot and related devices assembled from the wafer lot shall be rejected unless an appropriate determined corrective action to eliminate the failures mode has been implemented and the devices from the wafer lot are screened to eliminate the failure mode.

<u>Step</u>	<u>Method</u>	<u>Condition</u>
1	1026	Steady-state life: 1,000 hours minimum, $V_{CB} = 10$ dc, power and ambient shall be applied to achieve $T_J = +150^\circ\text{C}$ minimum using a minimum of $P_D = 75$ percent of maximum rated P_T as defined in 1.3. $n = 45$ devices, $c = 0$. The sample size may be increased and the test time decreased so long as the devices are stressed for a total of 45,000 device hours minimum, and the actual time of test is at least 340 hours.
2	1048	Blocking life, $T_A = +150^\circ\text{C}$, $V_{CB} = 80$ percent of rated voltage, 48 hours minimum. $n = 45$ devices, $c = 0$.
3	1032	High-temperature life (non-operating), $t = 340$ hours, $T_A = +200^\circ\text{C}$. $n = 22$, $c = 0$.

4.4.2.3 Group B sample selection. Samples selected from group B inspection shall meet all of the following requirements:

- a. For JAN, JANTX, JANTXV, and JANJ, samples shall be selected randomly from a minimum of three wafers (or from each wafer in the lot) from each wafer lot. For JANS, samples shall be selected from each inspection lot. See MIL-PRF-19500.
- b. Shall be chosen from an inspection lot that has been submitted to and passed table I, subgroup 2, conformance inspection. When the final lead finish is solder or any plating prone to oxidation at high temperature, the samples for life test (subgroups B4 and B5 for JANS, and group B for JAN, JANTX, JANTXV, and JANJ) may be pulled prior to the application of final lead finish.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table E-VII of MIL-PRF-19500, and in 4.4.3.1 (JANS) and 4.4.3.2 (JAN, JANTX, JANTXV, and JANJ) herein for group C testing. Electrical measurements (end-points) and delta requirements shall be in accordance with table I, subgroup 2 and 4.5.3 herein.

4.4.3.1 Group C inspection, table E-VII (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Test condition E, (not applicable for UA, UB, and UBC devices).
C6	1026	1,000 hours, $V_{CB} = 10$ V dc, power and ambient temperature shall be applied to the device to achieve $T_J = +150^\circ\text{C}$ minimum, and minimum power dissipation of 75 percent of max rated P_T (see 1.3 herein); $n = 45$, $c = 0$. The sample size may be increased and the test time decreased as long as the devices are stressed for a total of 45,000 device hours minimum, and the actual time of test is at least 340 hours.

MIL-PRF-19500/291R
w/AMENDMENT 2

4.4.3.2 Group C inspection, table E-VII (JAN, JANTX, JANTXV and JANJ) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	2036	Test condition E; not applicable for UA, UB, and UBC devices.
C5	3131	$R_{\theta JA}$ $R_{\theta JC}$ only (see 1.3).
C6		Not applicable.

4.4.3.3 Group C sample selection. Samples for steps in group C shall be chosen at random from any inspection lot containing the intended package type and lead finish procured to the same specification which is submitted to and passes table I tests for conformance inspection. Testing of a subgroup using a single device type enclosed in the intended package type shall be considered as complying with the requirements for that subgroup.

4.4.4 Group D inspection. Conformance inspection for hardness assured JANS, JANJ, and JANTXV types shall include the group D tests specified in table II herein. These tests shall be performed as required in accordance with MIL-PRF-19500 and method 1019 of MIL-STD-750, for total ionizing dose or method 1017 of MIL-STD-750 for neutron fluence as applicable (see 6.2 herein), except group D, subgroup 2 may be performed separate from other subgroups. Group D inspection may also be performed ahead of the screening lot using die selected in accordance with MIL-PRF-19500 and related documents. Alternate package options may also be substituted for the testing provided there is no adverse effect to the fluence profile.

4.4.5 Group E inspection. Group E inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table E-IX of MIL-PRF-19500 and as specified in table III herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. Delta measurements shall be in accordance with the applicable steps of 4.5.3.

4.5 Method of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Input capacitance. This test shall be conducted in accordance with method 3240 of MIL-STD-750, except the output capacitor shall be omitted.

4.5.3 Delta requirements. Delta requirements shall be as specified below:

Step	Inspection	MIL-STD-750		Symbol	Limit
		Method	Conditions		
1	Collector-base cutoff current	3036	Bias condition D, $V_{CB} = 50 \text{ V dc}$	ΔI_{CB02} (1)	100 percent of initial value or 10 nA dc, whichever is greater.
2	Forward current transfer ratio	3076	$V_{CE} = 10 \text{ V dc};$ $I_C = 150 \text{ mA dc};$ pulsed see 4.5.1	Δh_{FE4} (1)	± 25 percent change from initial reading.

(1) Devices which exceed the table I limits for this test shall not be accepted.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1 2/</u>						
Visual and mechanical inspection <u>3/</u>	2071	n = 45 devices, c = 0				
Solderability <u>3/ 4/</u>	2026	n = 15 leads, c = 0				
Resistance to solvents <u>3/ 4/ 5/</u>	1022	n = 15 devices, c = 0				
Temp cycling <u>3/ 4/</u>	1051	Test condition C, 25 cycles. n = 22 devices, c = 0				
Hermetic seal <u>4/</u> Fine leak Gross leak	1071	n = 22 devices, c = 0				
Electrical measurements <u>4/</u>		Table I, subgroup 2				
Bond strength <u>3/ 4/</u>	2037	Precondition T _A = +250°C at t = 24 hours or T _A = +300°C at t = 2 hours n = 11 wires, c = 0				
Decap internal visual (design verification) <u>4/</u>	2075	n = 4 devices, c = 0				
<u>Subgroup 2</u>						
Thermal impedance	3131	See 4.3.3	Z _{θJX}			°C/W
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 60 V dc	I _{CBO1}		10	μA dc
Cutoff current, emitter to base	3061	Bias condition D; V _{EB} = 5 V dc	I _{EBO1}		10	μA dc
Breakdown voltage, collector to emitter	3011	Bias condition D; I _C = 10 mA dc; pulsed (see 4.5.1)	V _{(BR)CEO}	60		V dc
Collector to emitter cutoff current	3041	Bias condition C; V _{CE} = 50 V dc	I _{CES}		50	nA dc
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 50 V dc	I _{CBO2}		10	nA dc
Emitter to base cutoff current	3061	Bias condition D; V _{EB} = 4 V dc	I _{EBO2}		50	nA dc

See footnotes at end of table.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE I. Group A inspection - Continued.

Inspection 1/	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 2</u> - Continued						
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 0.1 mA dc	h _{FE1}	40 75		
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 1.0 mA dc	h _{FE2}	40 100	175 450	
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 10 mA dc	h _{FE3}	40 100		
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 150 mA dc; pulsed (see 4.5.1)	h _{FE4}	40 100	120 300	
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 500 mA dc; pulsed (see 4.5.1)	h _{FE5}	40 50		
Collector-emitter saturation voltage	3071	I _C = 150 mA dc; I _B = 15 mA dc, pulsed (see 4.5.1)	V _{CE(sat)1}		0.4	V dc
Collector-emitter saturation voltage	3071	I _C = 500 mA dc; I _B = 50 mA dc; pulsed (see 4.5.1)	V _{CE(sat)2}		1.6	V dc
Base-emitter saturation voltage	3066	Test condition A; I _C = 150 mA dc; I _B = 15 mA dc; pulsed (see 4.5.1)	V _{BE(sat)1}	0.6	1.3	V dc
Base-emitter saturation voltage	3066	Test condition A; I _C = 500 mA dc; I _B = 50 mA dc; pulsed (see 4.5.1)	V _{BE(sat)2}		2.6	
<u>Subgroup 3</u>						
High temperature operation		T _A = +150°C				
Collector to base cutoff current	3036	Bias condition D; V _{CB} = 50 V dc	I _{CBO3}		10	μA dc
Low temperature operation		T _A = -55°C				
Forward-current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3076	V _{CE} = 10 V dc; I _C = 10 mA dc	h _{FE6}	20 50		

See footnotes at end of table.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u>						
Small-signal short-circuit forward current transfer ratio 2N2906A, L, UA, UB, UBC 2N2907A, L, UA, UB, UBC	3206	$V_{CE} = 10 \text{ V dc}; I_C = 1 \text{ mA dc};$ $f = 1 \text{ kHz}$	h_{fe}	40 100		
Magnitude of small- signal short- circuit forward current transfer ratio	3306	$V_{CE} = 20 \text{ V dc}; I_C = 20 \text{ mA dc};$ $f = 100 \text{ MHz}$	$ h_{fe} $	2.0		
Open circuit output capacitance	3236	$V_{CB} = 10 \text{ V dc}; I_E = 0;$ $100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	C_{obo}		8	pF
Input capacitance (output open- circuited)	3240	$V_{EB} = 2.0 \text{ V dc}; I_C = 0;$ $100 \text{ kHz} \leq f \leq 1 \text{ MHz}$ See 4.5.2.	C_{ibo}		30	pF
Saturated turn-on time		(See figure 17)	t_{on}		45	ns
Saturated turn-off time		(See figure 18)	t_{off}		300	ns
<u>Subgroups 5, 6, and 7</u>						
Not applicable						

1/ For sampling plan see MIL-PRF-19500.

2/ For resubmission of failed test subgroup of table I, double the sample size of the failed test or sequence of tests.
A failure in table I, subgroup 1 shall not require retest of the entire subgroup. Only the failed test shall be rerun upon submission.

3/ Separate samples may be used.

4/ Not required for JANS devices.

5/ Not required for laser marked devices.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE II. Group D inspection.

Inspection <u>1/ 2/ 3/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1 4/</u>						
Neutron irradiation	1017	Neutron exposure $V_{CES} = 0$ V				
Collector to base cutoff current	3036	Bias condition D; $V_{CB} = 60$ V dc	I_{CBO1}		20	μ A dc
Cutoff current, emitter to base	3061	Bias condition D; $V_{EB} = 5$ V dc	I_{EBO1}		20	μ A dc
Breakdown voltage, collector to emitter	3011	Bias condition D; $I_C = 10$ mA dc; pulsed (see 4.5.1)	$V_{(BR)CEO}$	60		V dc
Collector to emitter cutoff current	3041	Bias condition D; $V_{CE} = 50$ V dc	I_{CES}		100	nA dc
Collector to base cutoff current	3036	Bias condition D; $V_{CB} = 50$ V dc	I_{CBO2}		20	nA dc
Emitter to base cutoff current	3061	Bias condition D; $V_{EB} = 4$ V dc	I_{EBO2}		100	nA dc
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 0.1$ mA dc	$[h_{FE1}]$ <u>5/</u>	[20] [37.5]		
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 1.0$ mA dc	$[h_{FE2}]$ <u>5/</u>	[20] [50]	175 450	
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 10$ mA dc	$[h_{FE3}]$ <u>5/</u>	[20] [50]		
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 150$ mA dc	$[h_{FE4}]$ <u>5/</u>	[20] [50]	120 300	
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 500$ mA dc	$[h_{FE5}]$ <u>5/</u>	[20] [25]		
Collector-emitter saturation voltage	3071	$I_C = 150$ mA dc; $I_B = 15$ mA dc	$V_{CE(sat)1}$.46	V dc
Collector-emitter saturation voltage	3071	$I_C = 500$ mA dc; $I_B = 50$ mA dc	$V_{CE(sat)2}$		1.84	V dc
Base-emitter saturation voltage	3066	Test condition A; $I_C = 150$ mA dc; $I_B = 15$ mA dc; pulsed (see 4.5.1)	$V_{BE(sat)1}$	0.6	1.5	V dc
Base-emitter saturation voltage	3066	Test condition A; $I_C = 500$ mA dc; $I_B = 50$ mA dc; pulsed (see 4.5.1)	$V_{BE(sat)2}$		3.0	

See footnotes at end of table.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE II. Group D inspection - Continued.

Inspection <u>1/ 2/ 3/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 2</u>						
Total dose irradiation	1019	Gamma exposure $V_{CES} = 48$ V				
Collector to base cutoff current	3036	Bias condition D; $V_{CB} = 60$ V dc	I_{CBO1}		20	μ A dc
Cutoff current, emitter to base	3061	Bias condition D; $V_{EB} = 5$ V dc	I_{EBO1}		20	μ A dc
Breakdown voltage, collector to emitter	3011	Bias condition D; $I_C = 10$ mA dc; pulsed (see 4.5.1)	$V_{(BR)CEO}$	60		V dc
Collector to emitter cutoff current	3041	Bias condition D; $V_{CE} = 50$ V dc	I_{CES}		100	nA dc
Collector to base cutoff current	3036	Bias condition D; $V_{CB} = 50$ V dc	I_{CBO2}		20	nA dc
Emitter to base cutoff current	3061	Bias condition D; $V_{EB} = 4$ V dc	I_{EBO2}		100	nA dc
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 0.1$ mA dc	$[h_{FE1}] \underline{5/}$	[20] [37.5]		
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 1.0$ mA dc	$[h_{FE2}] \underline{5/}$	[20] [50]	175 400	
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 10$ mA dc	$[h_{FE3}] \underline{5/}$	[20] [50]		
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 150$ mA dc	$[h_{FE4}] \underline{5/}$	[20] [50]	120 300	
Forward-current transfer ratio M through H2N2906A M through H2N2907A	3076	$V_{CE} = 10$ V dc; $I_C = 500$ mA dc	$[h_{FE5}] \underline{5/}$	[20] [25]		
Collector-emitter saturation voltage	3071	$I_C = 150$ mA dc; $I_B = 15$ mA dc;	$V_{CE(sat)1}$.46	V dc
Collector-emitter saturation voltage	3071	$I_C = 500$ mA dc; $I_B = 50$ mA dc;	$V_{CE(sat)2}$		1.84	V dc

See footnotes at end of table.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE II. Group D inspection - Continued.

Inspection <u>1/</u> <u>2/</u> <u>3/</u>	MIL-STD-750		Symbol	Limit		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 2</u> - Continued.						
Base-emitter saturation voltage	3066	Test condition A; $I_C = 150$ mA dc; $I_B = 15$ mA dc; pulsed (see 4.5.1)	$V_{BE(sat)1}$	0.6	1.5	V dc
Base-emitter saturation voltage	3066	Test condition A; $I_C = 500$ mA dc; $I_B = 50$ mA dc; pulsed (see 4.5.1)	$V_{BE(sat)2}$		3.0	

1/ Tests to be performed on all devices receiving radiation exposure.

2/ For sampling plan, see MIL-PRF-19500.

3/ Electrical characteristics apply to the corresponding AL, UA, UB, and UBC suffix versions unless otherwise noted.

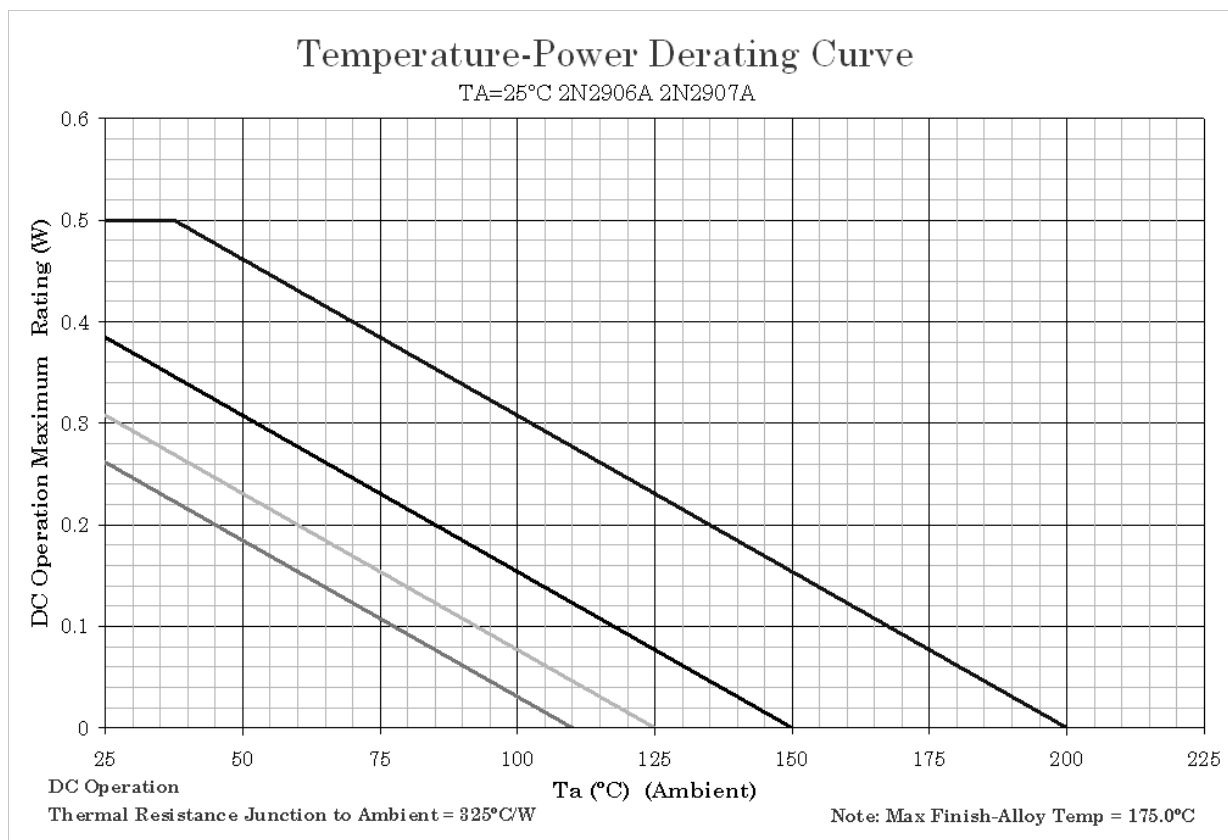
4/ See 6.2.f herein.

5/ See method 1019, of MIL-STD-750, for how to determine $[h_{FR}]$ by first calculating the delta ($1/h_{FE}$) from the pre- and post-radiation h_{FE} . Notice the $[h_{FE}]$ is not the same as h_{FE} and cannot be measured directly. The $[h_{FE}]$ value can never exceed the pre-radiation minimum h_{FE} that it is based upon.

MIL-PRF-19500/291R
w/AMENDMENT 2

TABLE III. Group E inspection (all quality levels) - for qualification only.

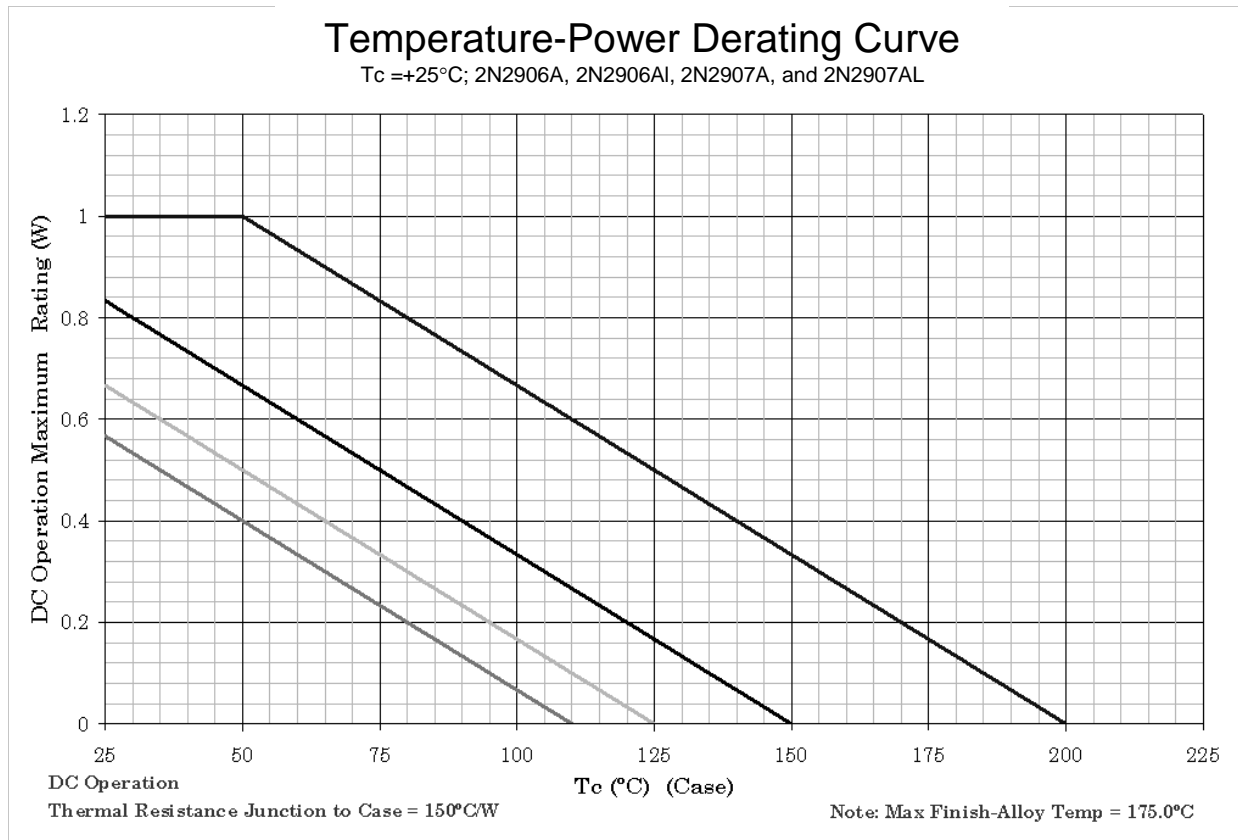
Inspection	MIL-STD-750		Qualification
	Method	Conditions	
<u>Subgroup 1</u>			
Temperature cycling (air to air)	1051	Test condition C, 500 cycles.	45 devices c = 0
Hermetic seal	1071		
Fine leak			
Gross leak			
Electrical measurements		See table I, subgroup 2 and 4.5.3 herein.	
<u>Subgroup 2</u>			45 devices c = 0
Intermittent life	1037	$V_{CB} = 10 \text{ V dc}$, 6,000 cycles. Adjust device current, or power, to achieve a minimum ΔT_J of 100°C .	
Electrical measurements		See table I, subgroup 2 and 4.5.3 herein.	
<u>Subgroup 4</u>			15 devices c = 0
Thermal resistance	3131	$R_{\theta JSP(IS)}$ may be calculated but shall be measured once in the same package with a similar die size to confirm calculations (may apply to multiple slash sheets). $R_{\theta JSP(AM)}$ need be calculated only.	
Thermal impedance curves		See MIL-PRF-19500, table E-IX, group E, subgroup 4.	Sample size N/A
<u>Subgroup 5</u>			
Not applicable			
<u>Subgroup 6</u>			3 devices c = 0
ESD	1020		
<u>Subgroup 8</u>			45 devices c = 0
Reverse stability	1033	Condition B.	



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq +125^\circ\text{C}$, and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

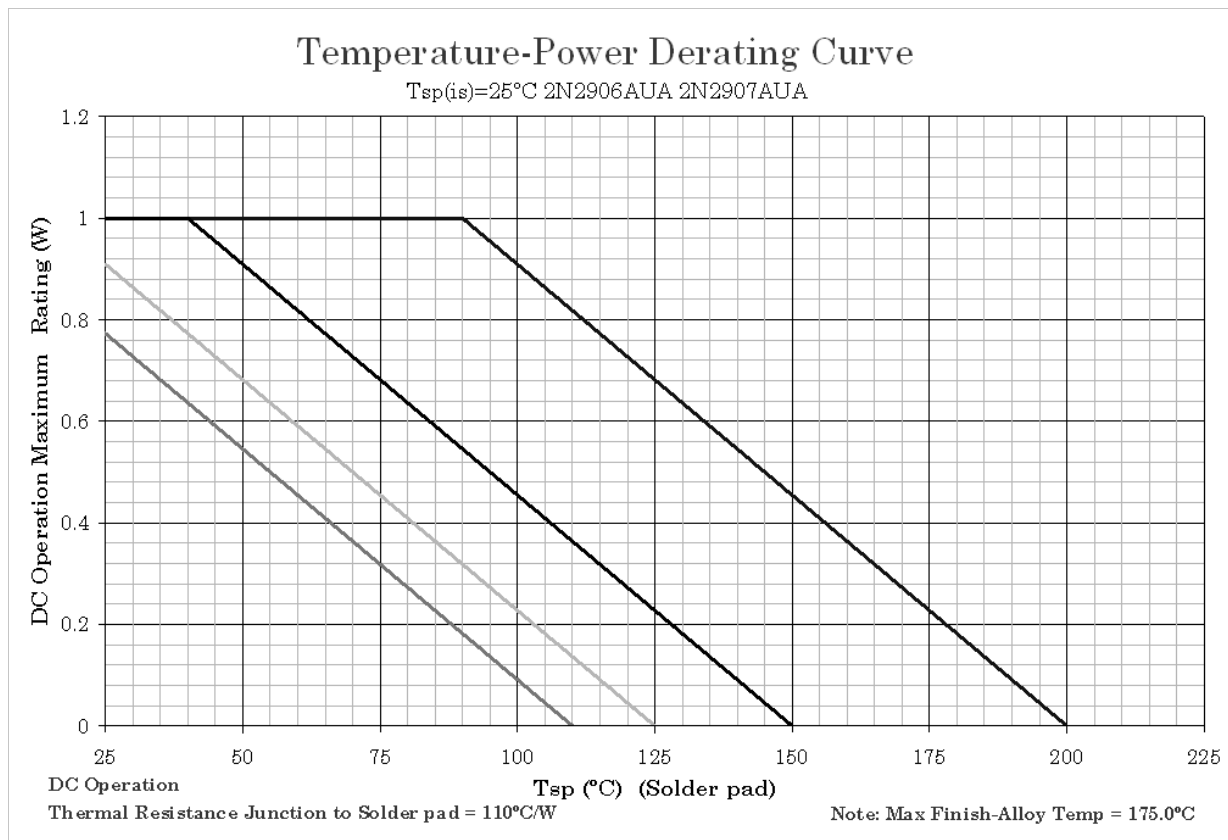
FIGURE 7. Temperature-power derating for 2N2906A, 2N2906AL, 2N2907A and 2N2907AL
($R_{\theta JA}$) leads .125 inch (3.18 mm) PCB (TO-18).



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq +125^\circ\text{C}$, and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

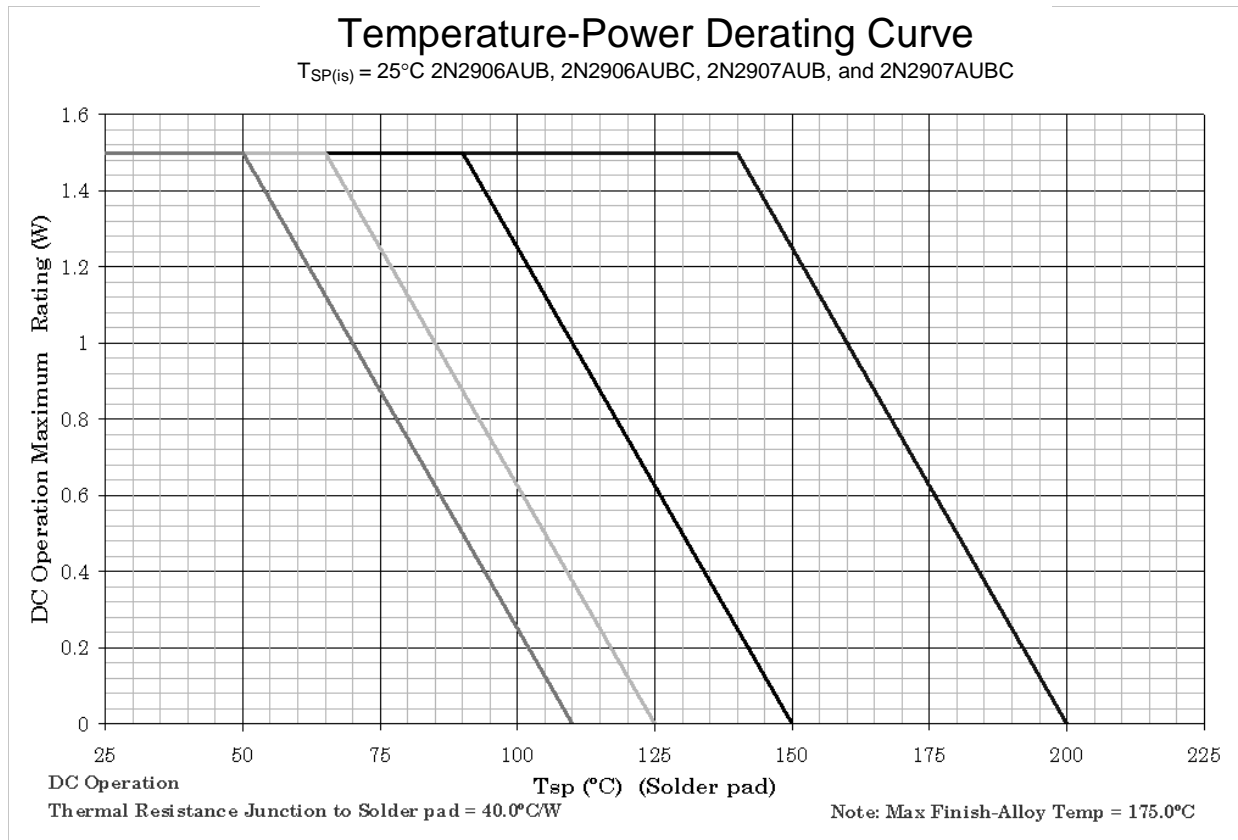
FIGURE 8. Temperature-power derating for 2N2906A, 2N2906AL, 2N2907A and 2N2907AL
($R_{\theta JC}$), base case mount (TO-18).



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^\circ\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq +125^\circ\text{C}$, and $+110^\circ\text{C}$ to show power rating where most users want to limit T_J in their application.

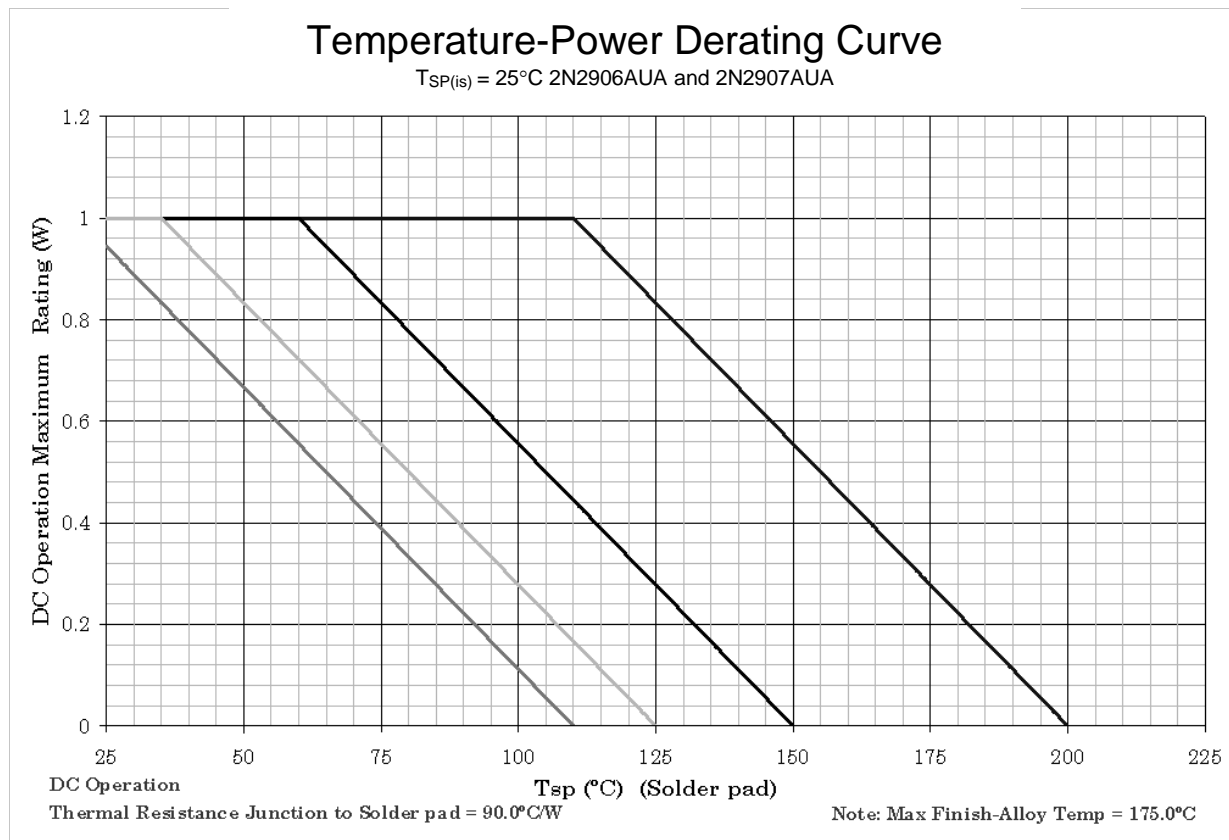
FIGURE 9. Temperature-power derating for 2N2906AUA and 2N2907AUA ($R_{\theta JSP(is)}$), infinite sink 4-points.



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_j$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_j allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_j \leq +150^{\circ}\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_j \leq +125^{\circ}\text{C}$, and $+110^{\circ}\text{C}$ to show power rating where most users want to limit T_j in their application.

FIGURE 10. Temperature-power derating for 2N2906AUA and 2N2907AUA ($R_{\theta JSP(AM)}$)
4-point solder pad (adhesive mount to PCB).



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at $\leq T_J$ specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum T_J allowed.
2. Derate design curve constrained by the maximum junction temperatures and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at $T_J \leq +150^{\circ}\text{C}$, where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at $T_J \leq +125^{\circ}\text{C}$, and $+110^{\circ}\text{C}$ to show power rating where most users want to limit T_J in their application.

FIGURE 11. Temperature-power derating for 2N2906AUB, 2N2906AUBC, 2N2907AUBC, and 2N2907AUB ($R_{\theta JSP(is)}$) infinite sink 3-point.

Maximum Thermal Impedance
2N2906A and 2N2907A TO-18 package with 0.125" lead mount to PCB

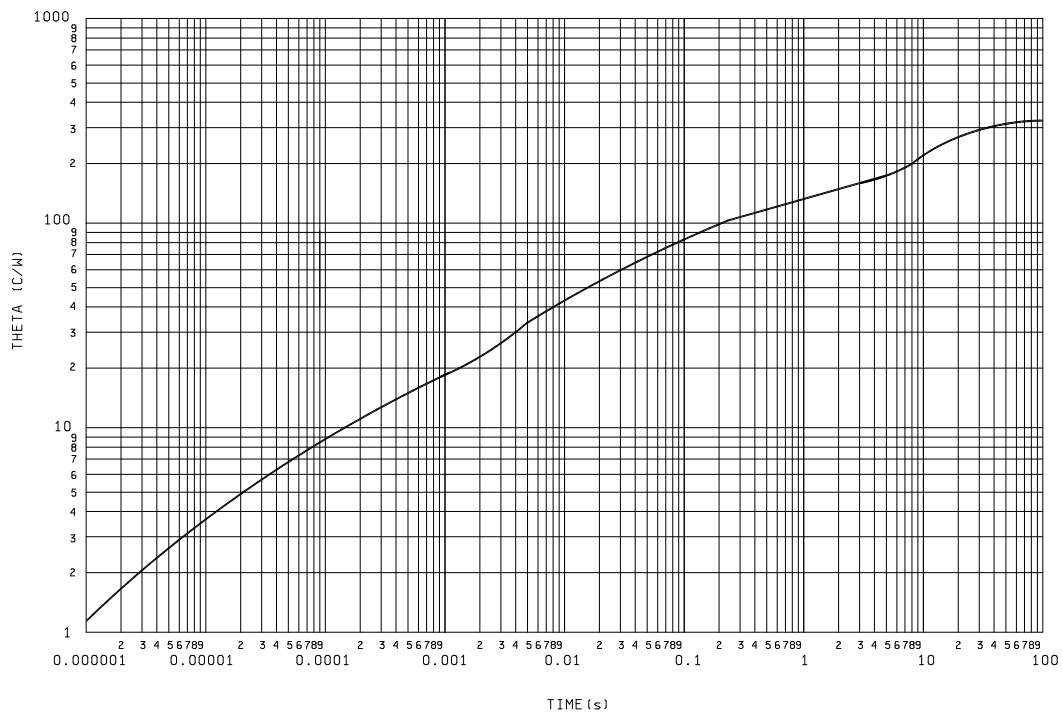


FIGURE 12. Thermal impedance graph ($R_{\theta JA}$) for 2N2906A, 2N2906AL, 2N2907A, and 2N2907AL (TO-18).

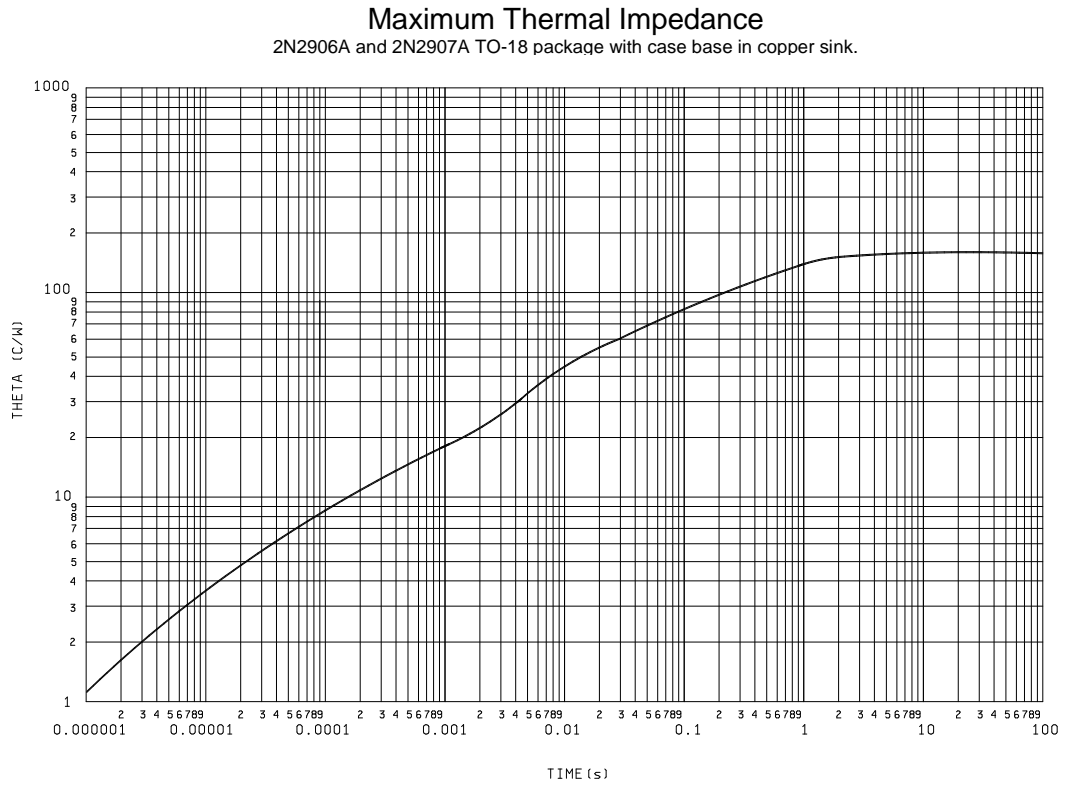


FIGURE 13. Thermal impedance graph ($R_{\theta JC}$) for 2N2906A, 2N2906AL, 2N2907A, and 2N2907AL (TO-18).

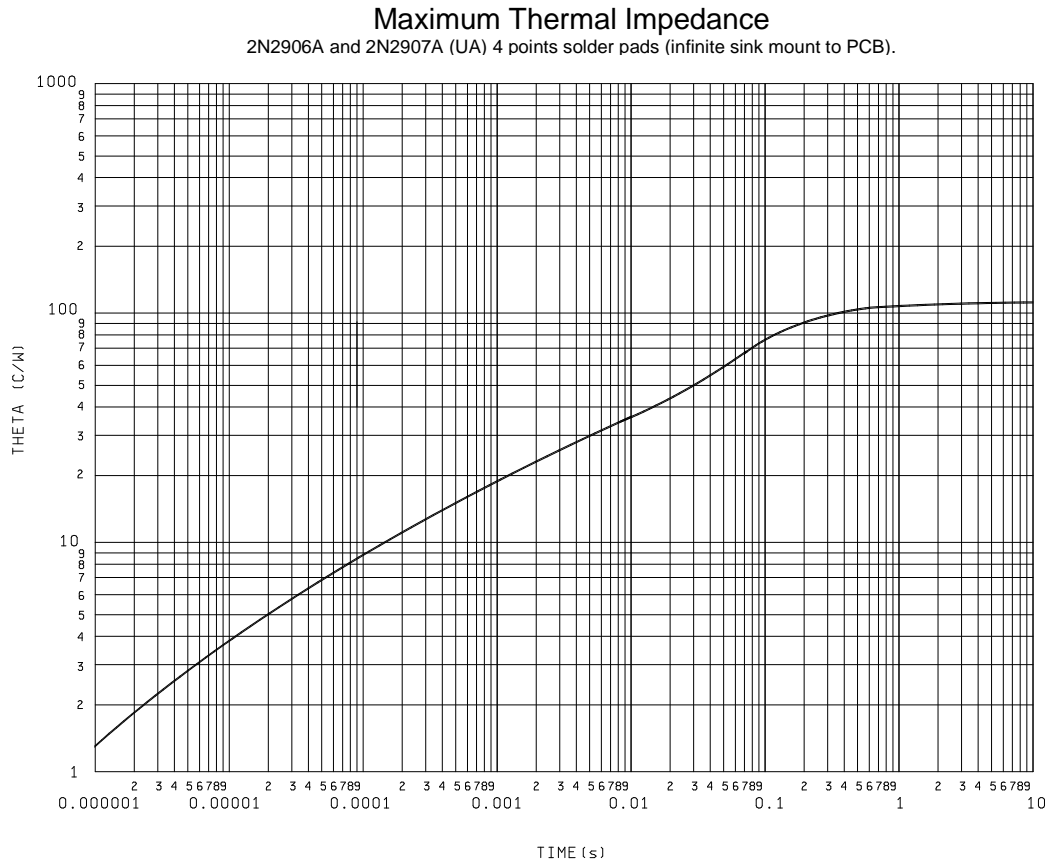


FIGURE 14. Thermal impedance graph ($R_{\theta\text{JSP}(t)}$) for 2N906A and 2N2907A (UA).

MIL-PRF-19500/291R
w/AMENDMENT 2

Maximum Thermal Impedance

2N2906A and 2N2907A (UA) 4 points solder pads (adhesive mount to PCB).

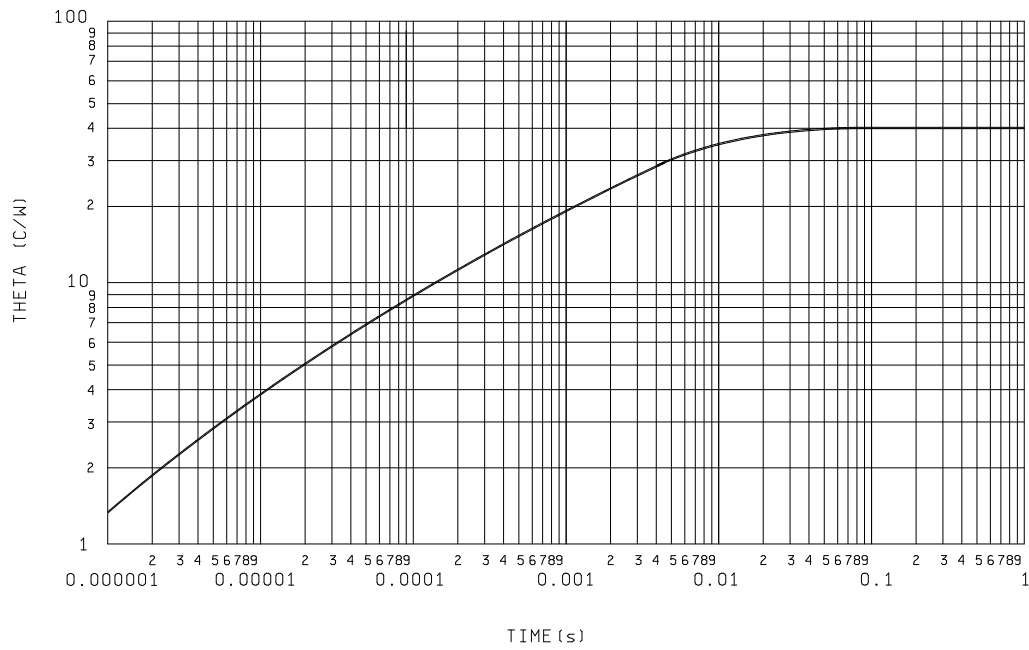


FIGURE 15. Thermal impedance graph ($R_{\theta JSP(AM)}$) for 2N906A and 2N2907A (UA).

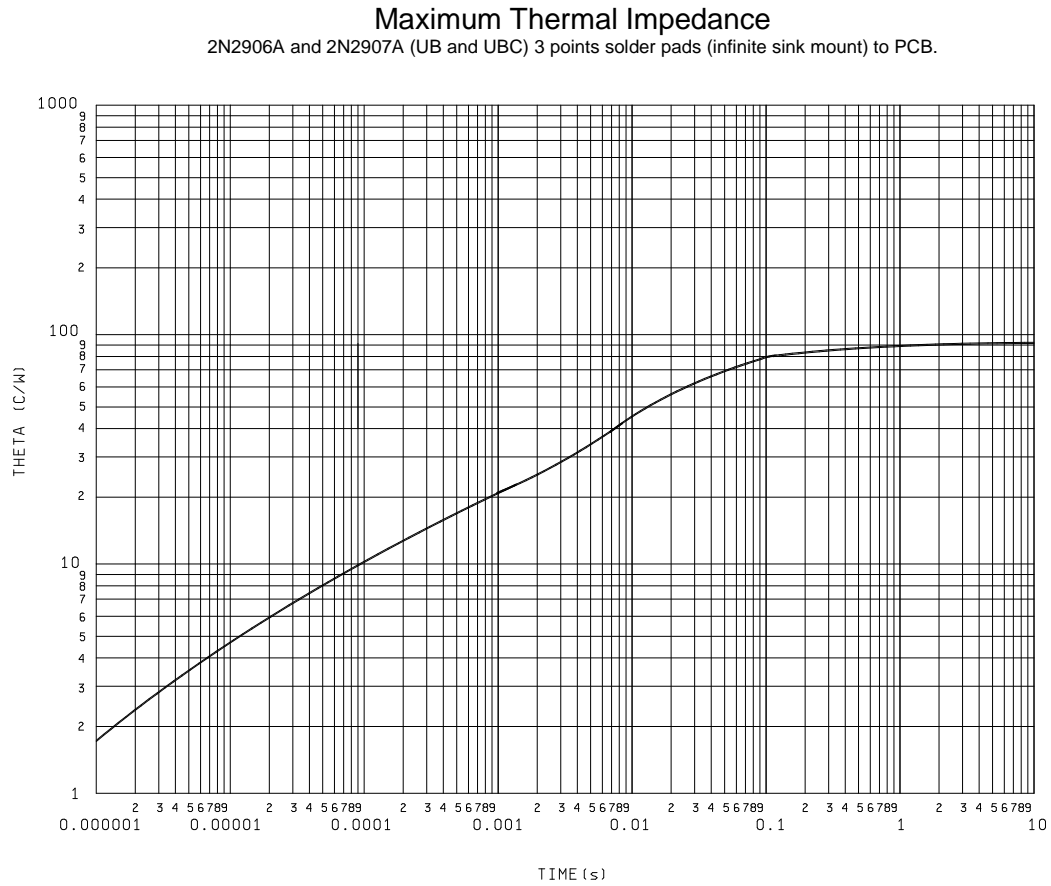
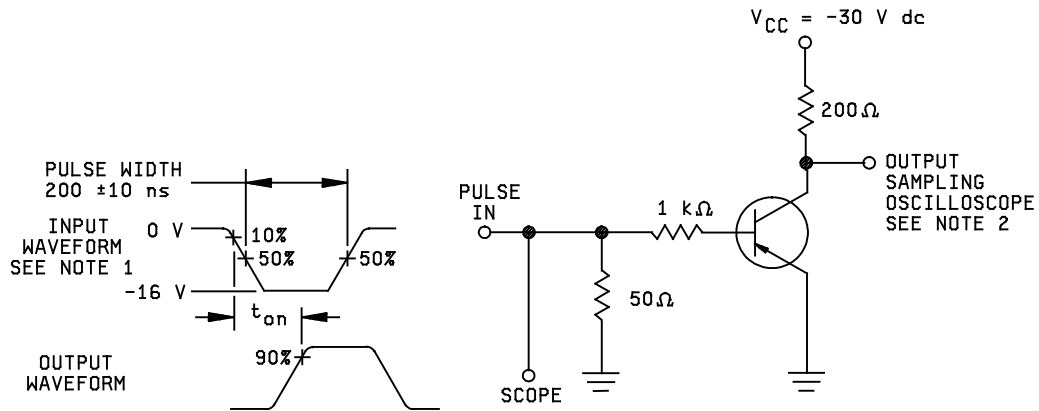


FIGURE 16. Thermal impedance graph ($R_{\theta JSP(S)}$) for 2N906A and 2N2907A (UB and UBC).

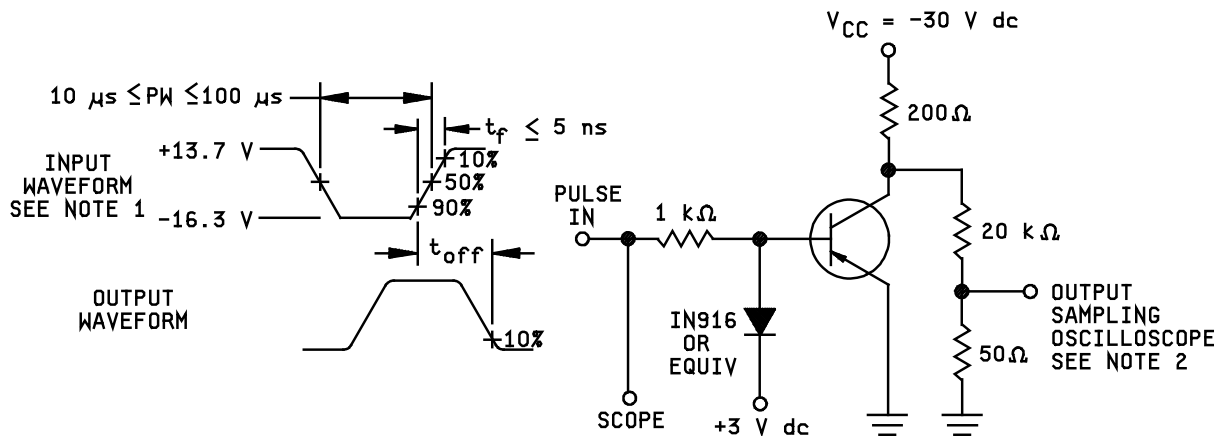
MIL-PRF-19500/291R
w/AMENDMENT 2



NOTES:

1. The rise time (t_r) of the applied pulse shall be ≤ 2.0 ns, duty cycle ≤ 2 percent and the generator source impedance shall be 50 ohms.
2. Sampling oscilloscope: $Z_{in} \geq 100$ K ohms, $C_{in} \leq 12$ pF, rise time ≤ 5 ns.

FIGURE 17. Saturated turn-on switching time test circuit.



NOTES:

1. The rise time (t_r) of the applied pulse shall be ≤ 2.0 ns, duty cycle ≤ 2 percent and the generator source impedance shall be 50 ohms.
2. Sampling oscilloscope: $Z_{in} \geq 100$ K ohms, $C_{in} \leq 12$ pF, rise time ≤ 5 ns.

FIGURE 18. Saturated turn-off switching time test circuit.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.1).
- d. Product assurance level and type designator.
- e. For die acquisition, the letter version must be specified (see figures 5 and 6).
- f. For acquisition of RHA designed devices, table II, subgroup 1 testing of group D is optional. If subgroup 1 testing is desired, it must be specified in the contract.

* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil. An online listing of products qualified to this specification may be found in the Qualified Products Database (QPD) at <https://assist.daps.dla.mil>.

6.4 Supersession information. Devices covered by this specification supersede the manufacturers' and users' Part or Identifying Number (PIN). The term Part or Identifying Number (PIN) is equivalent to the term part number which was previously used in this specification. This information in no way implies that manufacturers' PIN's are suitable as a substitute for the military PIN.

MIL-PRF-19500/291R
w/AMENDMENT 2

6.5 Suppliers of JANHC and JANKC die. The qualified JANHC and JANKC suppliers with the applicable letter version (example JANHCB2N2907A) will be identified on the QML.

Die ordering information (1) (2)		
PIN	Manufacturer	
	43611	34156
2N2906A 2N2907A	JANHCB2N2906A JANHCB2N2907A	JANHCD2N2906A JANHCD2N2907A

- (1) For JANKC level, replace JANHC with JANKC.
(2) JANHCA, JANKCA, JANHCC, and JANKCC versions are obsolete.

* 6.6 Amendment notations. The margins of this specification are marked with asterisks to indicate modifications generated by this amendment. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:
Army - CR
Navy - EC
Air Force - 85
NASA - NA
DLA - CC

Preparing activity:
DLA - CC
(Project 5961-2009-104)

Review activities:
Army - AR, MI, SM
Navy - AS, MC
Air Force - 19, 99

* NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <https://assist.daps.dla.mil>.